

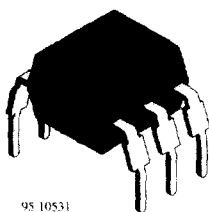
## Optocoupler with Phototransistor Output

Order Nos. and Classification table is on sheet 2.

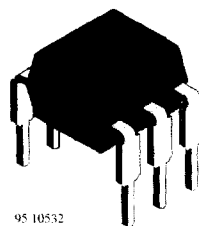
### Description

The CNY75(G) series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 6-lead plastic dual inline package.

The elements are mounted on one leadframe using a coplanar technique, providing a fixed distance between input and output for highest safety requirements.



95 10531



95 10532

### Applications

Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):

- For application class I - IV at mains voltage  $\leq 300$  V
- For application class I - III at mains voltage  $\leq 600$  V according to VDE 0884, table 2, suitable for:

**Switch-mode power supplies, computer peripheral interface, microprocessor-system interface, line receiver.**



**0884**

These couplers perform safety functions according to the following equipment standards:

- **VDE 0884**  
Optocoupler providing protective separation
- **VDE 0804**  
Telecommunication apparatus and data processing
- **VDE 0805/IEC 950/ 60950**  
Office machines (applied for reinforced isolation for mains voltages  $\leq 400$  V<sub>RMS</sub>)
- **VDE 0860/IEC 65**  
Safety for mains-operated electronic and related household apparatus

**Features**

According to VDE 0884

- Rated impulse voltage (transient overvoltage)  
 $V_{IOTM} = 6 \text{ kV peak}$
- Isolation test voltage (partial discharge test voltage)  
 $V_{pd} = 1.6 \text{ kV}$
- Rated isolation voltage (RMS includes DC)  
 $V_{IOWM} = 600 V_{RMS} (848 \text{ V peak})$
- Rated recurring peak voltage (repetitive)  
 $V_{IORM} = 600 V_{RMS}$
- Creeping current resistance according to VDE 0303/IEC 112  
Comparative Tracking Index: **CTI = 275**
- Thickness through insulation  $\geq 0.75 \text{ mm}$
- Further approvals:  
BS 415, BS 7002, SETI: IEC 950,  
UL 1577: File No: E 76222
- CTR offered in 3 groups
- Isolation materials according to UL94-VO
- Pollution degree 2 (DIN/VDE 0110 resp. IEC 664)
- Climatic classification  
55/100/21 (IEC 68 part 1)
- Special construction:  
Therefore extra low coupling capacity typical 0.3 pF,  
high Common Mode Rejection
- Low temperature coefficient of CTR

**Order Schematic**

| Part Numbers                  | CTR-Ranking |
|-------------------------------|-------------|
| CNY75A/ CNY75(G)A/ CNY75(G)AS | 63 to 125%  |
| CNY75B/ CNY75(G)B/ CNY75(G)BS | 100 to 200% |
| CNY75C/ CNY75(G)C/ CNY75(G)CS | 160 to 320% |

Suffix:        G = Leadform 10.16 mm  
                  S = Waterproof device

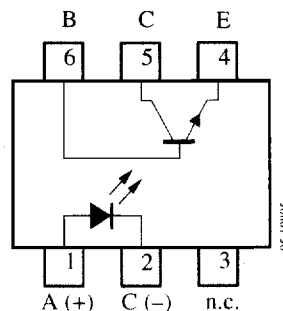
**Remarks**

A waterproof construction is recommended for couplers where a pure water cleaning process is used instead of a standard-soldering/ cleaning process. In this case please order the part numbers with the suffix "S". The waterproof construction corresponds with the coupling system "S", and does not belong to the part number itself.

Standard parts are marked with the letter "A".

This coupling system indicator "A" or "S" is in a separate (second) line of the marking.

**Pin Connection**



## Absolute Maximum Ratings

### Input (Emitter)

| Parameters            | Test Conditions                 | Symbol    | Value | Unit             |
|-----------------------|---------------------------------|-----------|-------|------------------|
| Reverse voltage       |                                 | $V_R$     | 5     | V                |
| Forward current       |                                 | $I_F$     | 60    | mA               |
| Forward surge current | $t_p \leq 10 \mu\text{s}$       | $I_{FSM}$ | 3     | A                |
| Power dissipation     | $T_{amb} \leq 25^\circ\text{C}$ | $P_{tot}$ | 100   | mW               |
| Junction temperature  |                                 | $T_j$     | 125   | $^\circ\text{C}$ |

### Output (Detector)

| Parameters                | Test Conditions                       | Symbol    | Value | Unit             |
|---------------------------|---------------------------------------|-----------|-------|------------------|
| Collector base voltage    |                                       | $V_{CBO}$ | 90    | V                |
| Collector emitter voltage |                                       | $V_{CEO}$ | 90    | V                |
| Emitter collector voltage |                                       | $V_{ECO}$ | 7     | V                |
| Collector current         |                                       | $I_C$     | 50    | mA               |
| Collector peak current    | $t_p/T = 0.5, t_p \leq 10 \text{ ms}$ | $I_{CM}$  | 100   | mA               |
| Power dissipation         | $T_{amb} \leq 25^\circ\text{C}$       | $P_{tot}$ | 150   | mW               |
| Junction temperature      |                                       | $T_j$     | 125   | $^\circ\text{C}$ |

### Coupler

| Parameters                      | Test Conditions                       | Symbol    | Value       | Unit             |
|---------------------------------|---------------------------------------|-----------|-------------|------------------|
| AC isolation test voltage (RMS) |                                       | $V_{IO}$  | 3.75        | kV               |
| Total power dissipation         | $T_{amb} \leq 25^\circ\text{C}$       | $P_{tot}$ | 250         | mW               |
| Ambient temperature range       |                                       | $T_{amb}$ | -55 to +100 | $^\circ\text{C}$ |
| Storage temperature range       |                                       | $T_{stg}$ | -55 to +125 | $^\circ\text{C}$ |
| Soldering temperature           | 2 mm from case, $t \leq 10 \text{ s}$ | $T_{sd}$  | 260         | $^\circ\text{C}$ |

**Maximum Safety Ratings<sup>1)</sup> (according to VDE 0884)**

**Input (Emitter)**

| Parameters      | Test Conditions | Symbol   | Value | Unit |
|-----------------|-----------------|----------|-------|------|
| Forward current |                 | $I_{si}$ | 130   | mA   |

**Output (Detector)**

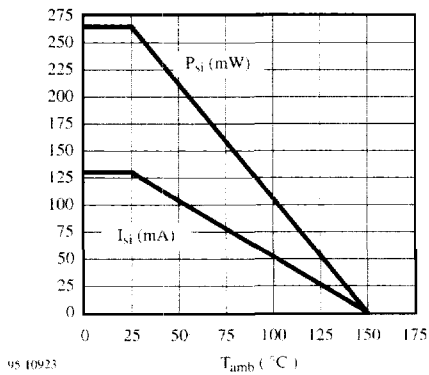
| Parameters        | Test Conditions                   | Symbol   | Value | Unit |
|-------------------|-----------------------------------|----------|-------|------|
| Power dissipation | $T_{amb} \leq 25^{\circ}\text{C}$ | $P_{si}$ | 265   | mW   |

**Coupler**

| Parameters            | Test Conditions | Symbol     | Value | Unit               |
|-----------------------|-----------------|------------|-------|--------------------|
| Rated impulse voltage |                 | $V_{IOTM}$ | 6     | kV                 |
| Safety temperature    |                 | $T_{si}$   | 150   | $^{\circ}\text{C}$ |

- 1) This device is used for protective separation against electrical shock only within the maximum safety ratings. This must be ensured by using protective circuits in the applications.

**Derating Diagram**



## Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$

### Input (Emitter)

| Parameters           | Test Conditions              | Symbol     | Min. | Typ. | Max. | Unit |
|----------------------|------------------------------|------------|------|------|------|------|
| Forward voltage      | $I_F = 50 \text{ mA}$        | $V_F$      |      | 1.25 | 1.6  | V    |
| Breakdown voltage    | $I_R = 100 \mu\text{A}$      | $V_{(BR)}$ | 5    |      |      | V    |
| Junction capacitance | $V_R = 0, f = 1 \text{ MHz}$ | $C_j$      |      | 50   |      | pF   |

### Output (Detector)

| Parameters                          | Test Conditions                  | Symbol        | Min. | Typ. | Max. | Unit |
|-------------------------------------|----------------------------------|---------------|------|------|------|------|
| Collector base breakdown voltage    | $I_C = 100 \mu\text{A}$          | $V_{(BR)CBO}$ | 90   |      |      | V    |
| Collector emitter breakdown voltage | $I_C = 1 \text{ mA}$             | $V_{(BR)CEO}$ | 90   |      |      | V    |
| Emitter collector breakdown voltage | $I_E = 100 \mu\text{A}$          | $V_{(BR)ECO}$ | 7    |      |      | V    |
| Collector emitter cut-off current   | $V_{CE} = 20 \text{ V}, I_F = 0$ | $I_{CEO}$     |      |      | 150  | nA   |

### Coupler

| Parameters                           | Test Conditions   | Type   | Symbol      | Min. | Typ. | Max. | Unit |
|--------------------------------------|---|--------|-------------|------|------|------|------|
| AC isolation test voltage (RMS)      | $f = 50 \text{ Hz}, t = 1 \text{ s}$                          |        | $V_{IO}$    | 3.75 |      |      | kV   |
| Collector emitter saturation voltage | $I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$                     |        | $V_{CEsat}$ |      |      | 0.3  | V    |
| Cut-off frequency                    | $V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$ |        | $f_c$       |      | 110  |      | kHz  |
| Coupling capacitance                 | $f = 1 \text{ MHz}$   |        | $C_k$       |      | 0.3  |      | pF   |
| $I_C/I_F$                            | $V_{CE} = 5 \text{ V}, I_F = 1 \text{ mA}$                    | CNY75A | CTR         | 0.15 |      |      |      |
|                                      |   | CNY75B | CTR         | 0.3  |      |      |      |
|                                      |   | CNY75C | CTR         | 0.6  |      |      |      |
| $I_C/I_F$                            | $V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}$                   | CNY75A | CTR         | 0.63 |      | 1.25 |      |
|                                      |   | CNY75B | CTR         | 1    |      | 2    |      |
|                                      |   | CNY75C | CTR         | 1.6  |      | 3.2  |      |

**Switching Characteristics (Typical Values)**

$V_S = 5\text{ V}$

| Type                              | $R_L = 100\ \Omega$ (see figure 1) |                    |                       |                    |                    |                        |                  | $R_L = 1\ \text{k}\Omega$ (see figure 2) |                        |                  |
|-----------------------------------|------------------------------------|--------------------|-----------------------|--------------------|--------------------|------------------------|------------------|--|------------------------|------------------|
|                                   | $t_d[\mu\text{s}]$                 | $t_r[\mu\text{s}]$ | $t_{on}[\mu\text{s}]$ | $t_s[\mu\text{s}]$ | $t_f[\mu\text{s}]$ | $t_{off}[\mu\text{s}]$ | $I_C[\text{mA}]$ | $t_{on}[\mu\text{s}]$                    | $t_{off}[\mu\text{s}]$ | $I_F[\text{mA}]$ |
| CNY75A<br>CNY75(G)A<br>CNY75(G)AS | 2.0                                | 2.5                | 4.5                   | 0.3                | 2.7                | 3.0                    | 10               | 10.0                                     | 25.0                   | 10               |
| CNY75B<br>CNY75(G)B<br>CNY75(G)BS | 2.5                                | 3.0                | 5.5                   | 0.3                | 3.7                | 4.0                    | 10               | 16.5                                     | 20.0                   | 10               |
| CNY75C<br>CNY75(G)C<br>CNY75(G)CS | 2.8                                | 4.2                | 7.0                   | 0.3                | 4.7                | 5.0                    | 10               | 11                                       | 37.5                   | 10               |

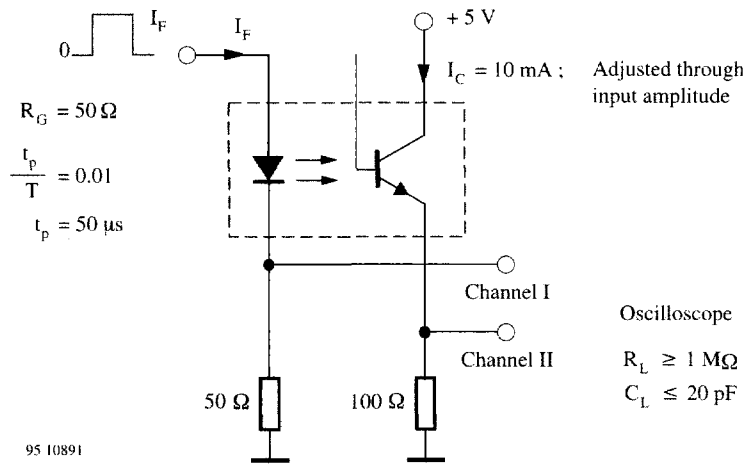


Figure 1. Test circuit, non-saturated operation

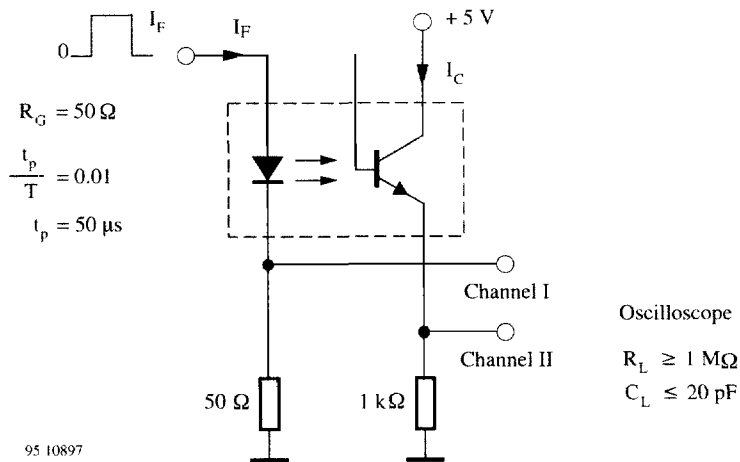


Figure 2. Test circuit, saturated operation

## Insulation Rated Parameters (according to VDE 0884)

| Parameters                     |                        | Test Conditions  | Symbol            | Min.      | Typ. | Max. | Unit     |
|--------------------------------|------------------------|--|-------------------|-----------|------|------|----------|
| Partial discharge test voltage | Routine test           | 100%, $t_{\text{test}} = 1 \text{ s}$  | $V_{\text{pd}}$   | 1.6       |      |      | kV       |
|                                | Lot test (sample test) | $t_{\text{Tr}} = 10 \text{ s}$ ,<br>$t_{\text{test}} = 60 \text{ s}$<br>(see figure 3)                   | $V_{\text{IOTM}}$ | 6         |      |      | kV       |
|                                |                        |  | $V_{\text{pd}}$   | 1.3       |      |      | kV       |
| Insulation resistance          |                        | $V_{\text{IO}} = 500 \text{ V}$  | $R_{\text{IO}}$   | $10^{12}$ |      |      | $\Omega$ |
|                                |                        | $V_{\text{IO}} = 500 \text{ V}$ ,<br>$T_{\text{amb}} \leq 100^\circ\text{C}$                             | $R_{\text{IO}}$   | $10^{11}$ |      |      | $\Omega$ |
|                                |                        | $V_{\text{IO}} = 500 \text{ V}$ ,<br>$T_{\text{amb}} \leq 150^\circ\text{C}$<br>(construction test only) | $R_{\text{IO}}$   | $10^9$    |      |      | $\Omega$ |

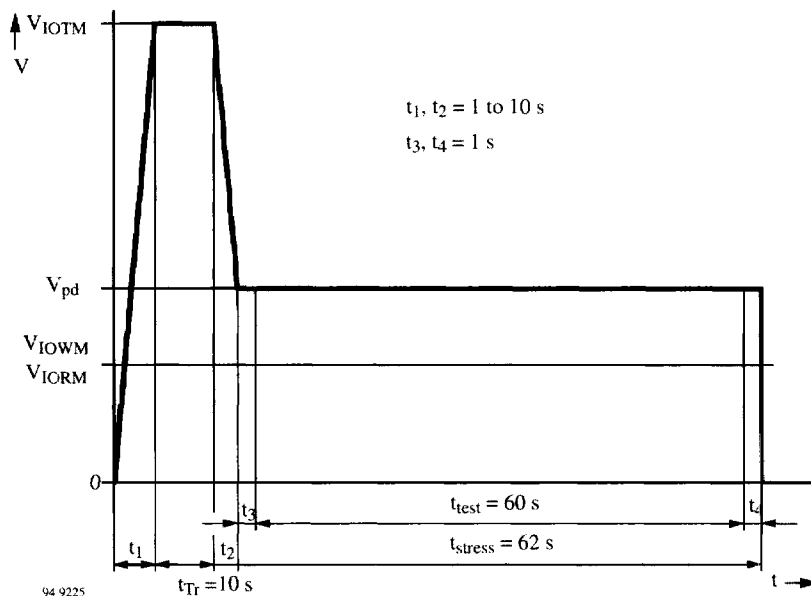


Figure 3. Test pulse diagram for sample test according to DIN VDE 0884

**Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)**

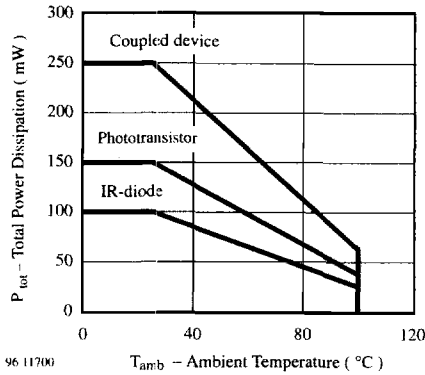


Figure 4. Total Power Dissipation vs. Ambient Temperature

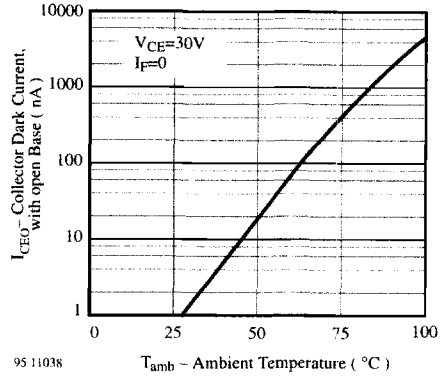


Figure 7. Collector Dark Current vs. Ambient Temperature

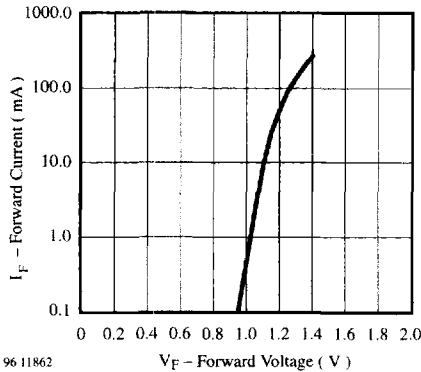


Figure 5. Forward Current vs. Forward Voltage

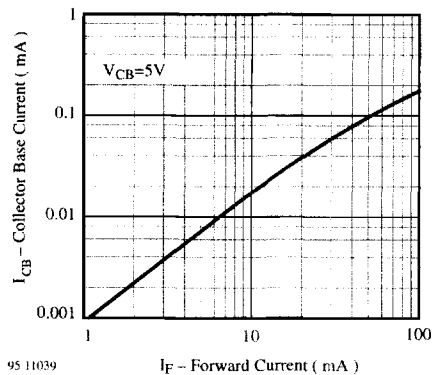


Figure 8. Collector Base Current vs. Forward Current

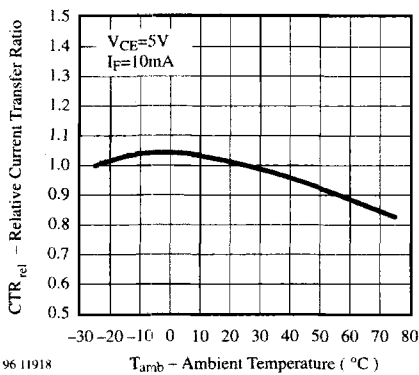


Figure 6. Rel. Current Transfer Ratio vs. Ambient Temperature

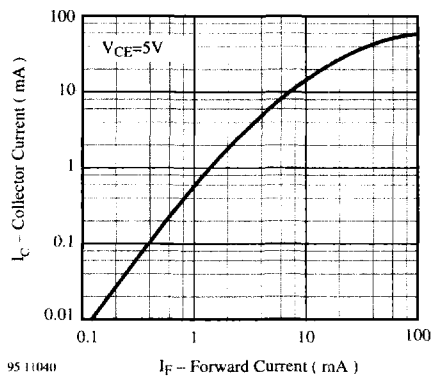


Figure 9. Collector Current vs. Forward Current



## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)

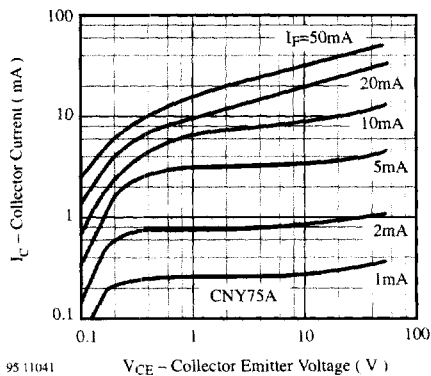


Figure 10. Collector Current vs. Collector Emitter Voltage

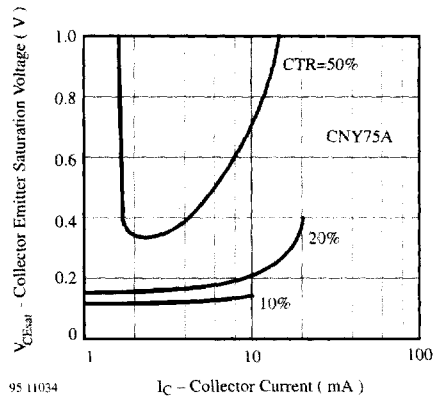


Figure 13. Collector Emitter Sat. Voltage vs. Collector Current

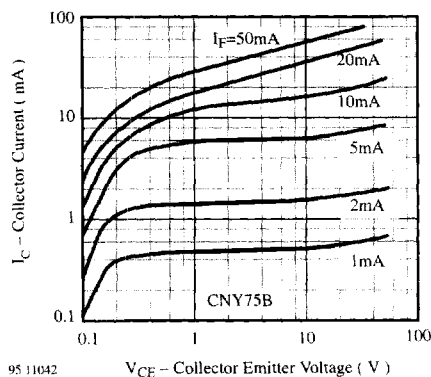


Figure 11. Collector Current vs. Collector Emitter Voltage

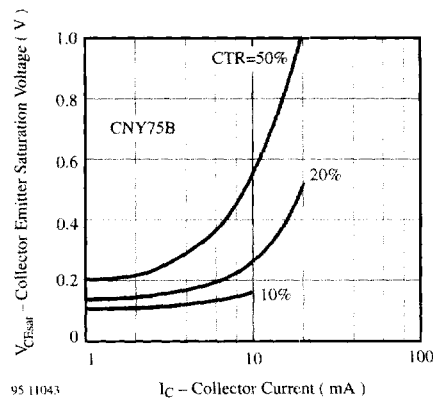


Figure 14. Collector Emitter Sat. Voltage vs. Collector Current

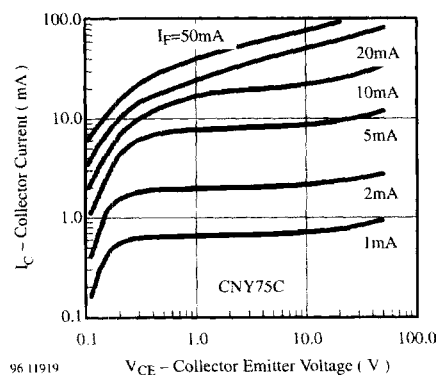


Figure 12. Collector Current vs. Collector Emitter Voltage

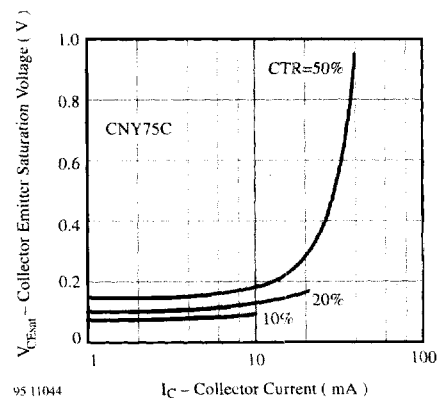


Figure 15. Collector Emitter Sat. Voltage vs. Collector Current

**Typical Characteristics** ( $T_{amb} = 25^{\circ}C$ , unless otherwise specified)

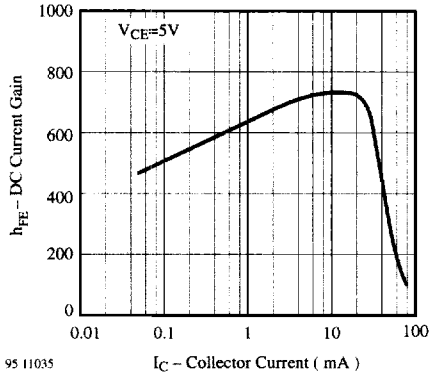


Figure 16. DC Current Gain vs. Collector Current

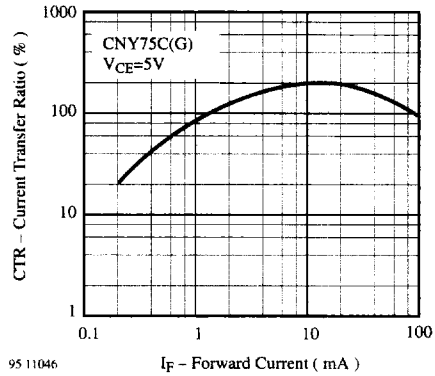


Figure 19. Current Transfer Ratio vs. Forward Current

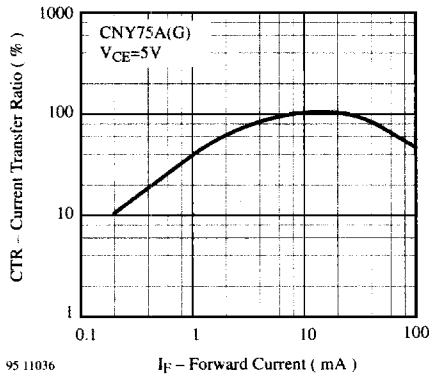


Figure 17. Current Transfer Ratio vs. Forward Current

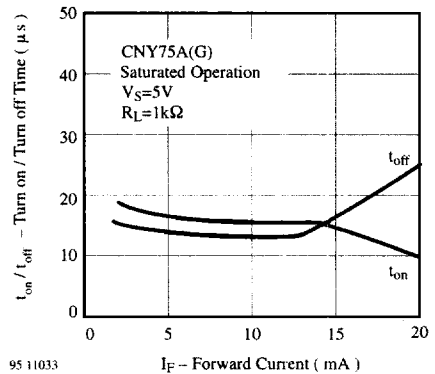


Figure 20. Turn on / off Time vs. Forward Current

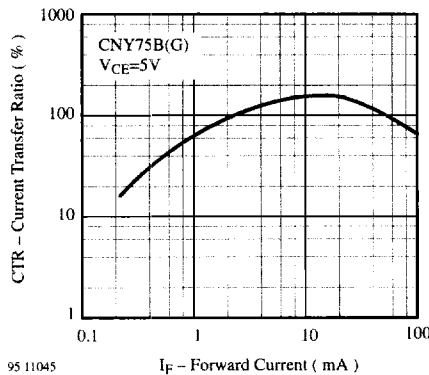


Figure 18. Current Transfer Ratio vs. Forward Current

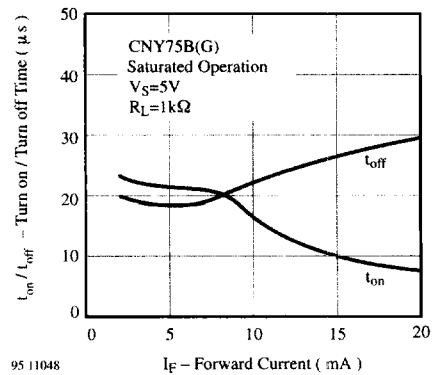


Figure 21. Turn on / off Time vs. Forward Current

## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)

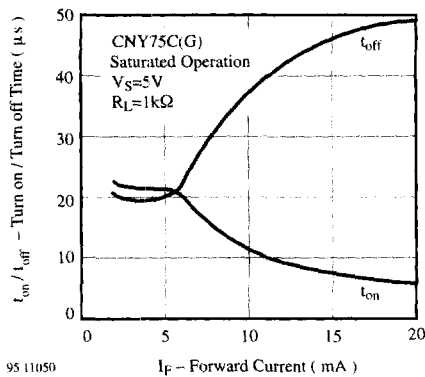


Figure 22. Turn on / off Time vs. Forward Current

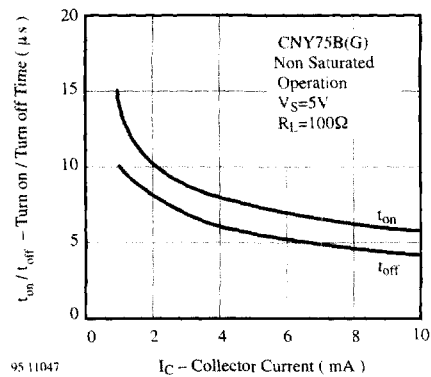


Figure 24. Turn on / off Time vs. Collector Current

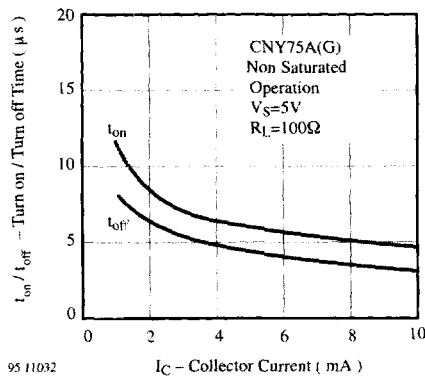


Figure 23. Turn on / off Time vs. Collector Current

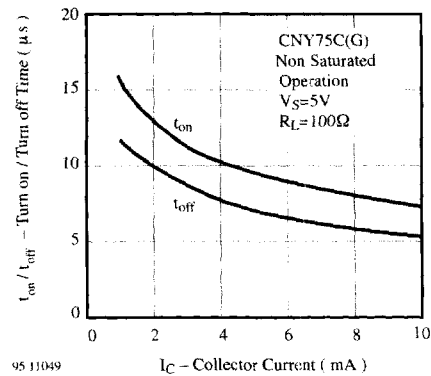
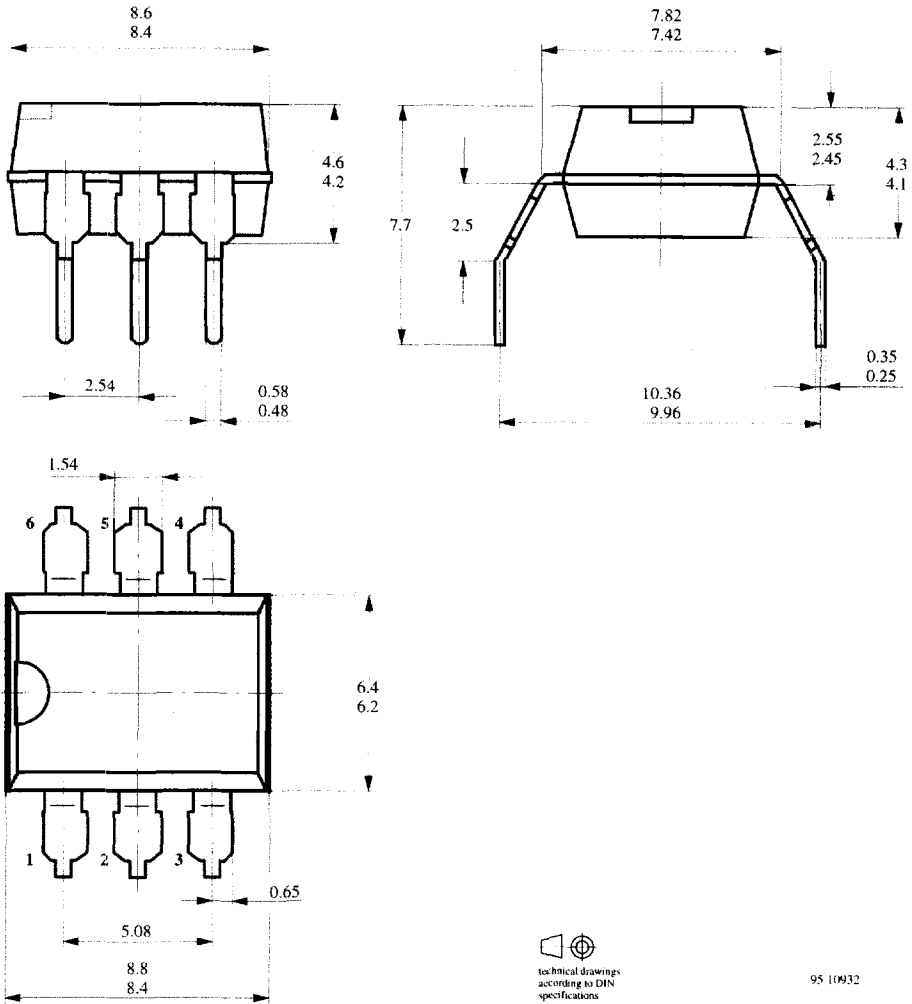


Figure 25. Turn on / off Time vs. Collector Current

**Dimensions in mm**

Leadform 10.16. mm (G-type)



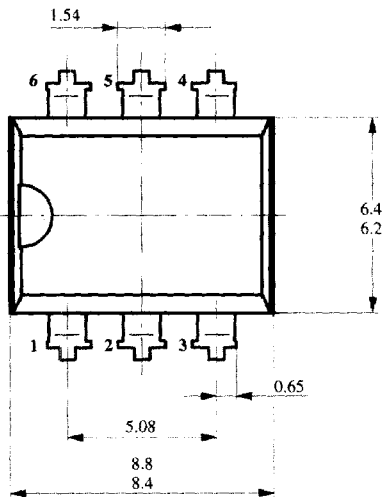
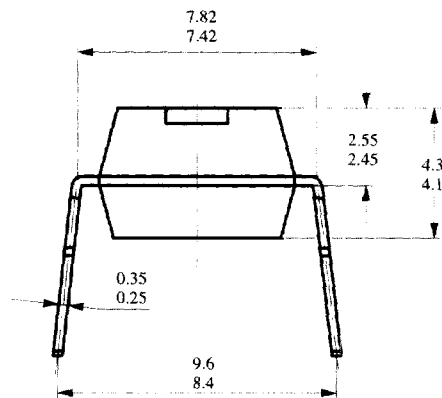
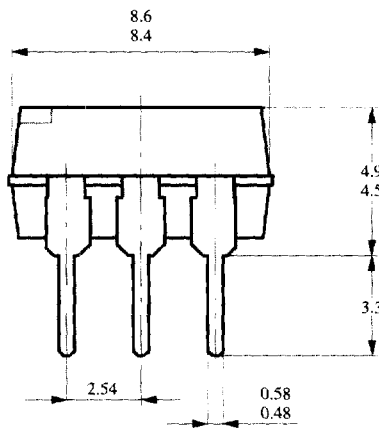
technical drawings  
according to DIN  
specifications

95 10932

# CNY75(G) Series

**TEMIC**  
Semiconductors

## Dimensions in mm



  
technical drawings  
according to DIN  
specifications

95 10931